

# Huadong Gan

## List of Publications by Year in descending order

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20  
papers

3,508  
citations

932766

10  
h-index

752256

20  
g-index

20  
all docs

20  
docs citations

20  
times ranked

3270  
citing authors

#	ARTICLE	IF	CITATIONS
1	A perpendicular-anisotropy CoFeB/MgO magnetic tunnel junction. <i>Nature Materials</i> , 2010, 9, 721-724.	13.3	3,020
2	MgO barrier-perpendicular magnetic tunnel junctions with CoFe/Pd multilayers and ferromagnetic insertion layers. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	130
3	RECENT PROGRESS OF PERPENDICULAR ANISOTROPY MAGNETIC TUNNEL JUNCTIONS FOR NONVOLATILE VLSI. <i>Spin</i> , 2012, 02, 1240003.	0.6	63
4	Origin of the collapse of tunnel magnetoresistance at high annealing temperature in CoFeB/MgO perpendicular magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	55
5	Tunnel magnetoresistance properties and film structures of double MgO barrier magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	49
6	Photocurrent response in a double barrier structure with quantum dots/quantum well inserted in central well. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 33, 355-358.	1.3	34
7	High performance perpendicular magnetic tunnel junction with Co/Ir interfacial anisotropy for embedded and standalone STT-MRAM applications. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	34
8	Boron Composition Dependence of Magnetic Anisotropy and Tunnel Magnetoresistance in MgO/CoFe(B) Based Stack Structures. <i>IEEE Transactions on Magnetics</i> , 2012, 48, 3829-3832.	1.2	28
9	Perpendicular magnetic tunnel junction with thin CoFeB/Ta/Co/Pd/Co reference layer. <i>Applied Physics Letters</i> , 2014, 105, 192403.	1.5	24
10	Perpendicular Magnetic Tunnel Junctions with CoFe/Pd Multilayer Electrodes and an MgO Barrier. <i>IEEE Transactions on Magnetics</i> , 2009, 45, 3476-3479.	1.2	19
11	Tunnel Magnetoresistance Properties of Double MgO-Barrier Magnetic Tunnel Junctions With Different Free-Layer Alloy Compositions and Structures. <i>IEEE Transactions on Magnetics</i> , 2011, 47, 1567-1570.	1.2	10
12	Different dielectric breakdown mechanisms for RF-MgO and naturally oxidized MgO. <i>Applied Physics Express</i> , 2014, 7, 083002.	1.1	9
13	Ferromagnetic nature of (Ga, Cr)As epilayers revealed by magnetic circular dichroism. <i>Solid State Communications</i> , 2011, 151, 456-459.	0.9	8
14	Zero-field spin transfer oscillators based on magnetic tunnel junction having perpendicular polarizer and planar free layer. <i>AIP Advances</i> , 2016, 6, 125305.	0.6	8
15	Photoinduced voltage shift in a three-barrier, two-well resonant tunneling structure integrated with a 1.2- $\mu$ m-thick n-type GaAs layer. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 28, 242-246.	1.3	4
16	Two opposite gradients of hole density in as-grown and annealed (Ga,Mn)As layers. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 308, 313-317.	1.0	4
17	Growth Parameter Dependence of Structural Characterizations of Diluted Magnetic Semiconductor (Ga, Cr)As. <i>IEEE Transactions on Magnetics</i> , 2008, 44, 2692-2695.	1.2	3
18	Influences of As flux on the lattice constants, magnetic and transport properties of (Ga, Mn)As epilayers. <i>Solid State Communications</i> , 2007, 141, 453-458.	0.9	2

#	ARTICLE	IF	CITATIONS
19	Dramatic reduction of read disturb through pulse width control in spin torque random access memory. Applied Physics Letters, 2013, 103, 142419.	1.5	2
20	Perpendicular magnetic tunneling junction switching dynamic modes, extreme events, and performance scaling. Applied Physics Letters, 2017, 110, .	1.5	2